

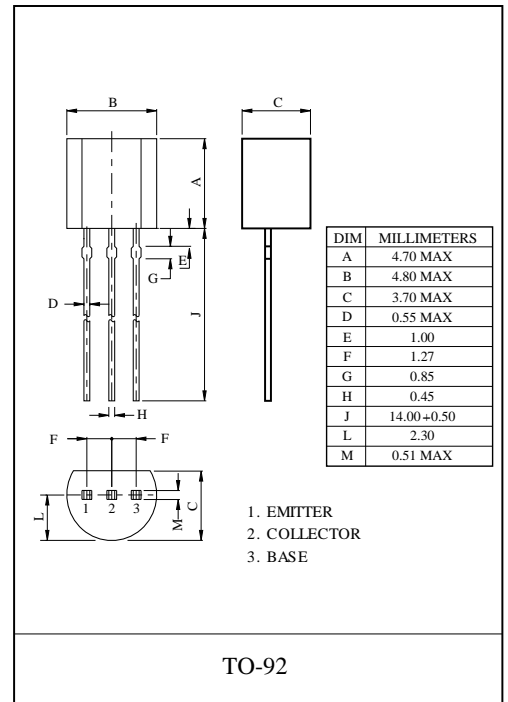
TRANSISTOR (NPN)

FEATURES

- General Purpose Switching Application
- Complementary to FTA1266.

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current	0.15	A
P _C	Collector Power Dissipation	0.625	W
R _{θJA}	Thermal Resistance From Junction To Ambient	200	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =0.1mA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =5mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA, I _C =0	5			V
Collector cut-off current	I _{CB0}	V _{CB} =60V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =6V, I _C =2mA	70		700	
	h _{FE(2)}	V _{CE} =6V, I _C =150mA	25			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =10mA			0.25	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =100mA, I _B =10mA			1	V
Transition frequency	f _T	V _{CE} =10V, I _C =1mA	80			MHz
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz			3.5	pF

CLASSIFICATION OF h_{FE(1)}

RANK	O	Y	GR	BL
RANGE	70-140	120-240	200-400	300-700

Typical Characteristics

